

**60V P-CHANNEL ENHANCEMENT MODE MOSFET**
**Product Summary**

| $V_{(BR)DSS}$ | $R_{DS(on)}$             | $I_D$<br>$T_A = +25^\circ C$ |
|---------------|--------------------------|------------------------------|
| -60V          | 390mΩ @ $V_{GS} = -10V$  | -2.3A                        |
|               | 595mΩ @ $V_{GS} = -4.5V$ | -1.9A                        |

**Description and Applications**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

**Features and Benefits**

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

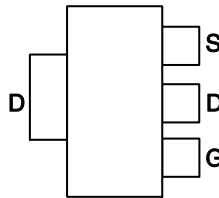
**Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

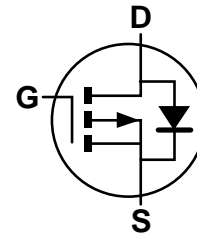
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

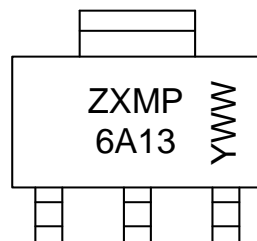
**Ordering Information (Note 4)**

| Product     | Marking  | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|----------|--------------------|-----------------|-------------------|
| ZXMP6A13GTA | ZXMP6A13 | 7                  | 12              | 1,000             |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**

SOT223



ZXMP 6A13 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 5= 2015)  
 WW or  $\bar{W}W$  = Week Code (01-53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

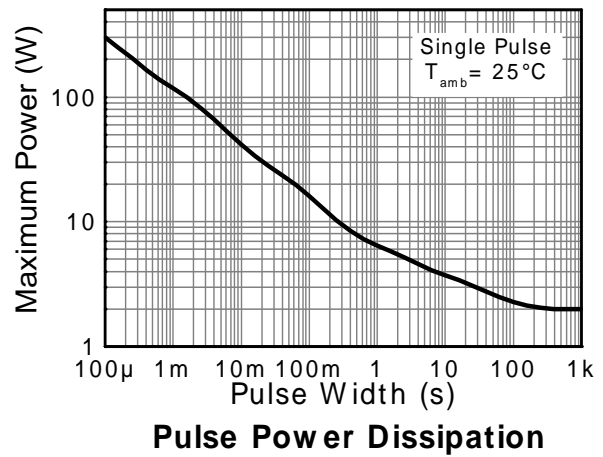
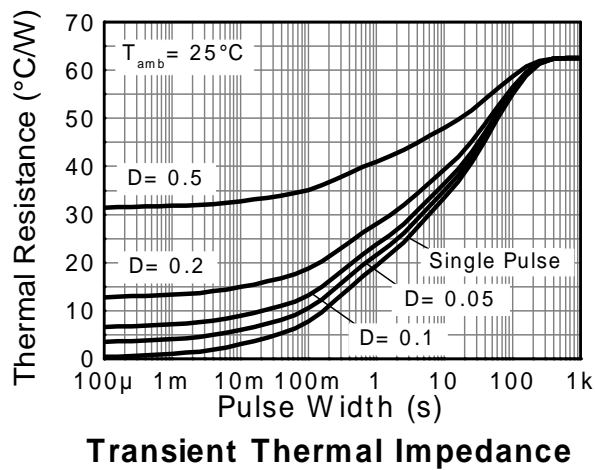
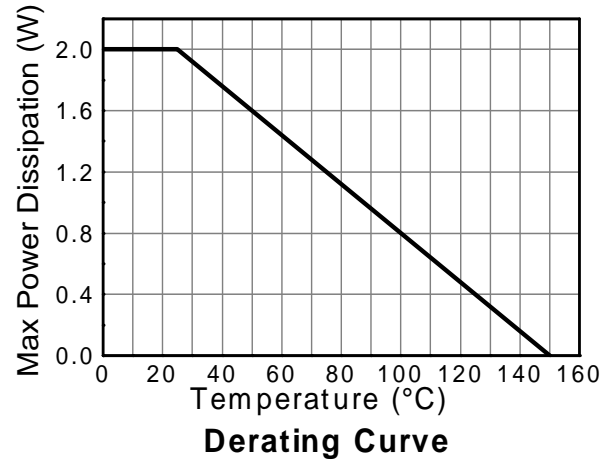
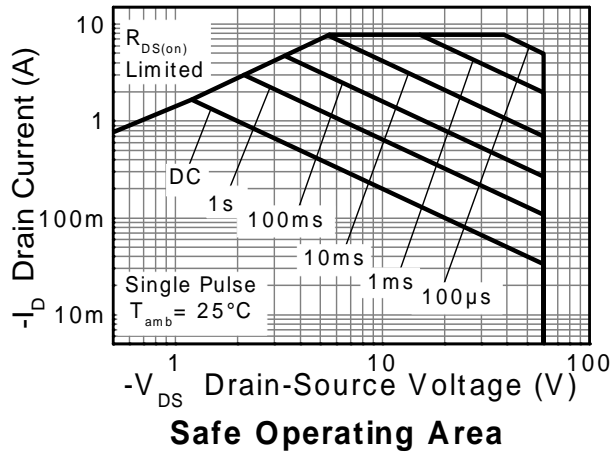
| Characteristic                         |                       |                                 | Symbol           | Value | Unit |
|--|-----------------------|---------------------------------|------------------|-------|------|
| Drain-Source Voltage                   |                       |                                 | V <sub>DSS</sub> | -60   | V    |
| Gate-Source Voltage                    |                       |                                 | V <sub>GS</sub>  | ±20   | V    |
| Continuous Drain Current               | V <sub>GS</sub> = 10V | (Note 6)                        | I <sub>D</sub>   | -2.3  | A    |
|  |                       | T <sub>A</sub> = +70°C (Note 6) |                  | -1.9  |      |
|  |                       | (Note 5)                        |                  | -1.7  |      |
| Pulsed Drain Current                   | V <sub>GS</sub> = 10V | (Note 7)                        | I <sub>DM</sub>  | -7.8  | A    |
| Continuous Source Current (Body Diode) |                       |                                 | I <sub>S</sub>   | -4.1  | A    |
| Pulsed Source Current (Body Diode)     |                       |                                 | I <sub>SM</sub>  | -7.8  | A    |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                          |          | Symbol                            | Value      | Unit  |
|---|----------|-----------------------------------|------------|-------|
| Power Dissipation                       | (Note 5) | P <sub>D</sub>                    | 2.0        | W     |
|   |          |                                   | 16         |       |
| Linear Derating Factor                  | (Note 6) |                                   | 3.9        | mW/°C |
|   |          |                                   | 31         |       |
| Thermal Resistance, Junction to Ambient | (Note 5) | R <sub>θJA</sub>                  | 62.5       | °C/W  |
|   | (Note 6) |                                   | 32.0       |       |
| Thermal Resistance, Junction to Lead    | (Note 8) | R <sub>θJL</sub>                  | 9.8        |       |
| Operating and Storage Temperature Range |          | T <sub>J</sub> , T <sub>STG</sub> | -55 to 150 | °C    |

- Notes:
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as Note 5, except the device is measured at t ≤ 10 sec.
  - Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
  - Thermal resistance from junction to solder-point (at the end of the drain lead).

## Thermal Characteristics

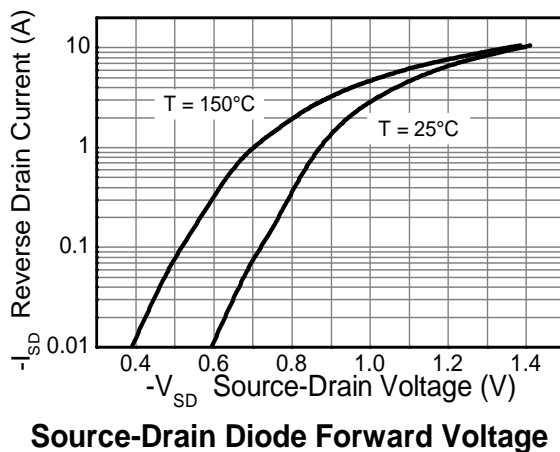
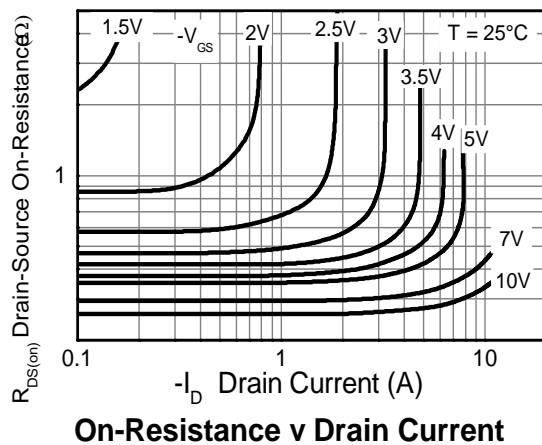
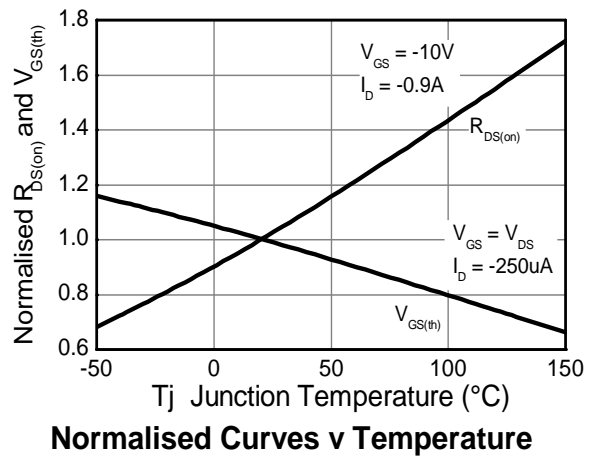
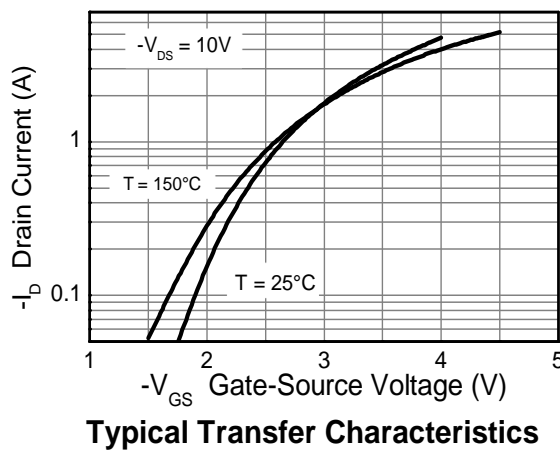
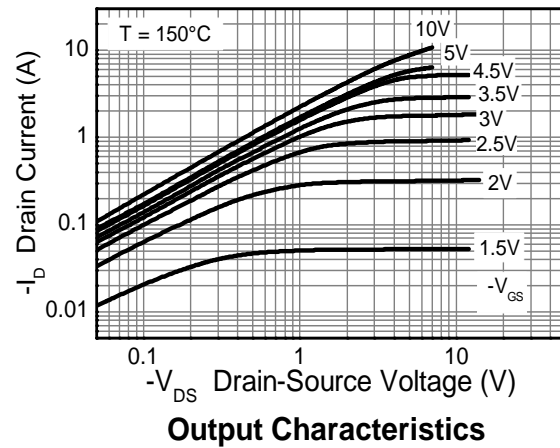
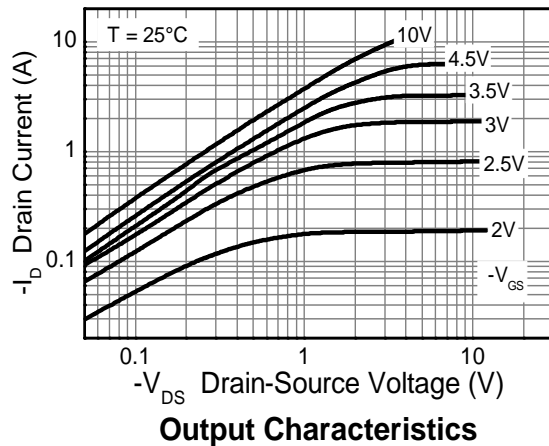


**Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

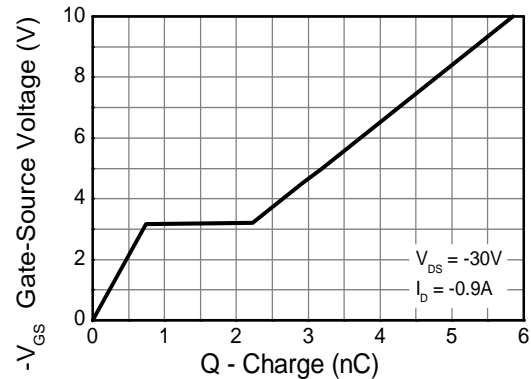
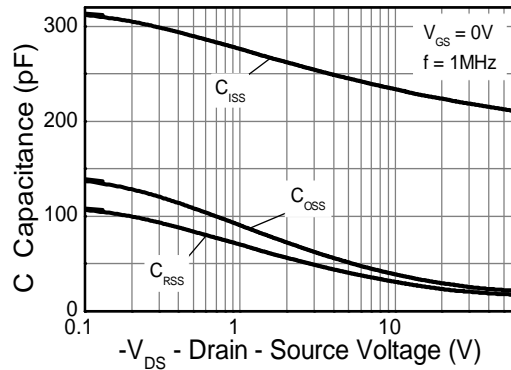
| Characteristic                             | Symbol               | Min  | Typ   | Max   | Unit | Test Condition  |  |
|--|----------------------|------|-------|-------|------|---|--|
| OFF CHARACTERISTICS                        |                      |      |       |       |      |   |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>    | -60  | —     | —     | V    | I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V   |  |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>     | —    | —     | -0.5  | μA   | V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V  |  |
| Gate-Source Leakage                        | I <sub>GSS</sub>     | —    | —     | ±100  | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V  |  |
| ON CHARACTERISTICS                         |                      |      |       |       |      |   |  |
| Gate Threshold Voltage                     | V <sub>GS(th)</sub>  | -1.0 | —     | -3.0  | V    | I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>                                    |  |
| Static Drain-Source On-Resistance (Note 9) | R <sub>DS (ON)</sub> | —    | —     | 0.390 | Ω    | V <sub>GS</sub> = -10V, I <sub>D</sub> = -0.9A  |  |
|  |                      |      |       | 0.595 |      | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.8A   |  |
| Forward Transconductance (Notes 9 & 10)    | g <sub>fs</sub>      | —    | 1.8   | —     | S    | V <sub>DS</sub> = -15V, I <sub>D</sub> = -0.9A  |  |
| Diode Forward Voltage (Note 9)             | V <sub>SD</sub>      | —    | -0.85 | -0.95 | V    | I <sub>S</sub> = -0.8A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C                          |  |
| Reverse Recovery Time (Note 10)            | t <sub>rr</sub>      |      | 21.1  | —     | ns   | I <sub>S</sub> = -0.9A, di/dt = 100A/μs,  |  |
| Reverse Recovery Charge (Note 10)          | Q <sub>rr</sub>      | —    | 19.3  | —     | nC   | T <sub>J</sub> = +25°C  |  |
| DYNAMIC CHARACTERISTICS (Note 10)          |                      |      |       |       |      |   |  |
| Input Capacitance                          | C <sub>iss</sub>     | —    | 219   | —     | pF   | V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V<br>f = 1MHz                                      |  |
| Output Capacitance                         | C <sub>oss</sub>     | —    | 25.7  | —     | pF   |   |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>     | —    | 20.5  | —     | pF   |   |  |
| Total Gate Charge (Note 11)                | Q <sub>g</sub>       | —    | 2.9   | —     | nC   | V <sub>GS</sub> = -4.5V   | V <sub>DS</sub> = -30V<br>I <sub>D</sub> = -0.9A |
| Total Gate Charge (Note 11)                | Q <sub>g</sub>       | —    | 5.9   | —     | nC   | V <sub>GS</sub> = -10V  |  |
| Gate-Source Charge (Note 11)               | Q <sub>gs</sub>      | —    | 0.74  | —     | nC   |   |  |
| Gate-Drain Charge (Note 11)                | Q <sub>gd</sub>      | —    | 1.5   | —     | nC   |   |  |
| Turn-On Delay Time (Note 11)               | t <sub>D(on)</sub>   | —    | 1.6   | —     | ns   | V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V<br>I <sub>D</sub> = -1A, R <sub>G</sub> ≅ 6.0Ω |  |
| Turn-On Rise Time (Note 11)                | t <sub>r</sub>       | —    | 2.2   | —     | ns   |   |  |
| Turn-Off Delay Time (Note 11)              | t <sub>D(off)</sub>  | —    | 11.2  | —     | ns   |   |  |
| Turn-Off Fall Time (Note 11)               | t <sub>f</sub>       | —    | 5.7   | —     | ns   |   |  |

- Notes:
9. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
  10. For design aid only, not subject to production testing.
  11. Switching characteristics are independent of operating junction temperatures.

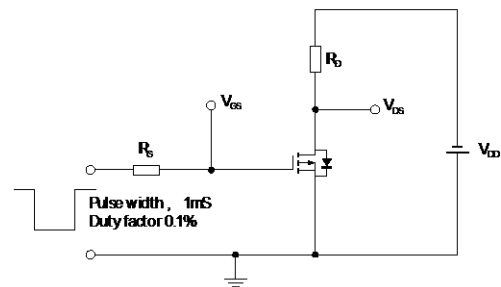
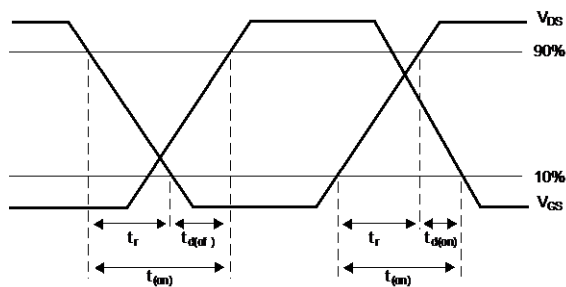
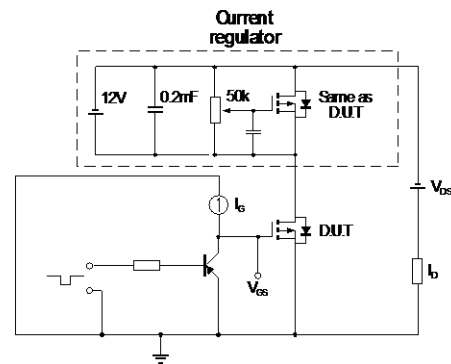
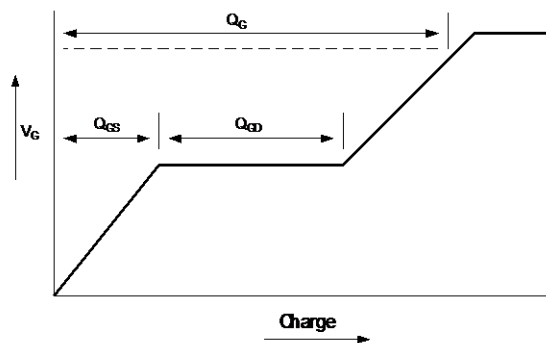
## Typical Characteristics



## Typical Characteristics (cont.)

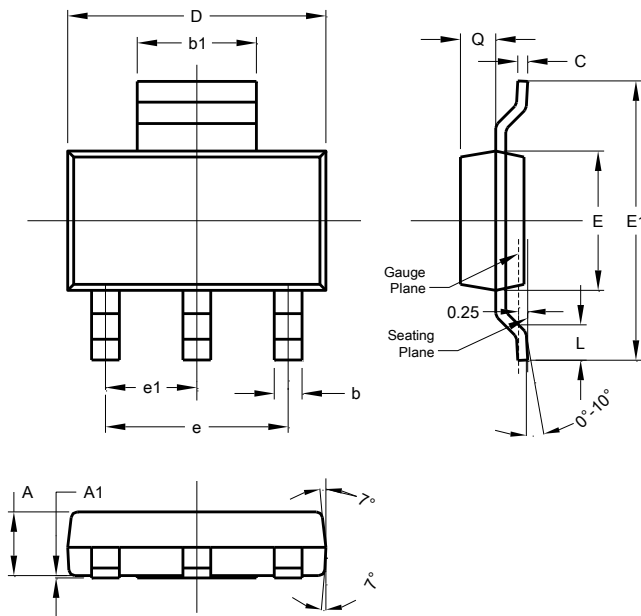


## Test Circuits



## Package Outline Dimensions

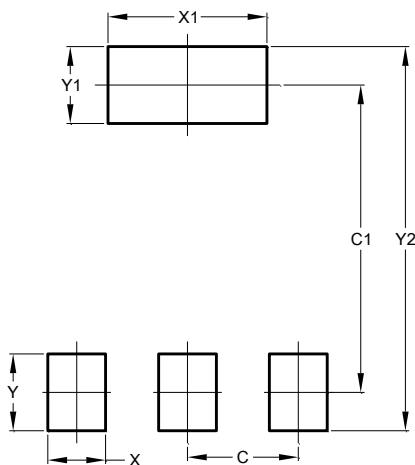
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



| SOT223               |       |      |      |
|----------------------|-------|------|------|
| Dim                  | Min   | Max  | Typ  |
| A                    | 1.55  | 1.65 | 1.60 |
| A1                   | 0.010 | 0.15 | 0.05 |
| b                    | 0.60  | 0.80 | 0.70 |
| b1                   | 2.90  | 3.10 | 3.00 |
| C                    | 0.20  | 0.30 | 0.25 |
| D                    | 6.45  | 6.55 | 6.50 |
| E                    | 3.45  | 3.55 | 3.50 |
| E1                   | 6.90  | 7.10 | 7.00 |
| e                    | -     | -    | 4.60 |
| e1                   | -     | -    | 2.30 |
| L                    | 0.85  | 1.05 | 0.95 |
| Q                    | 0.84  | 0.94 | 0.89 |
| All Dimensions in mm |       |      |      |

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 2.30          |
| C1         | 6.40          |
| X          | 1.20          |
| X1         | 3.30          |
| Y          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8.00          |

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